

**TGD N-Channel Super Trench Power MOSFET****Description**

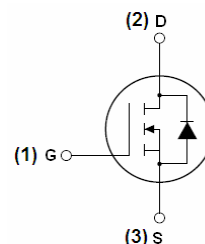
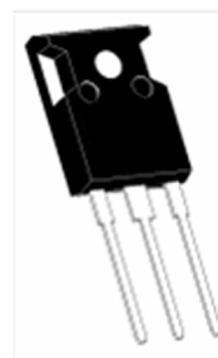
The TGDP01T30T uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{DS(on)}$ and Q_g . This device is ideal for high-frequency switching and synchronous rectification.

General Features

- $V_{DS} = 100V, I_D = 300A$
 $R_{DS(on)} < 2.1m\Omega @ V_{GS} = 10V$
- Excellent gate charge x $R_{DS(on)}$ product
- Very low on-resistance $R_{DS(on)}$
- 175 °C operating temperature
- Pb-free lead plating
- 100% UIS tested

Application

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

**Schematic diagram****TO-247 top view****100% UIS TESTED!****100% ΔV_{ds} TESTED!****Package Marking and Ordering Information**

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
TGDP01T30T	TGDP01T30T	TO-247	-	-	-

Absolute Maximum Ratings ($T_C = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	300	A
Drain Current-Continuous($T_C = 100^\circ C$)	$I_D(100^\circ C)$	220	A
Pulsed Drain Current	I_{DM}	1200	A
Maximum Power Dissipation	P_D	520	W
Derating factor		3.47	W/ $^\circ C$
Single pulse avalanche energy ^(Note 5)	E_{AS}	3400	mJ
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 175	$^\circ C$

Thermal Characteristic

Thermal Resistance, Junction-to-Case ^(Note 2)	$R_{\theta JC}$	0.29	$^\circ C/W$
--	-----------------	------	--------------



Electrical Characteristics ($T_C=25^{\circ}\text{C}$ unless otherwise noted)

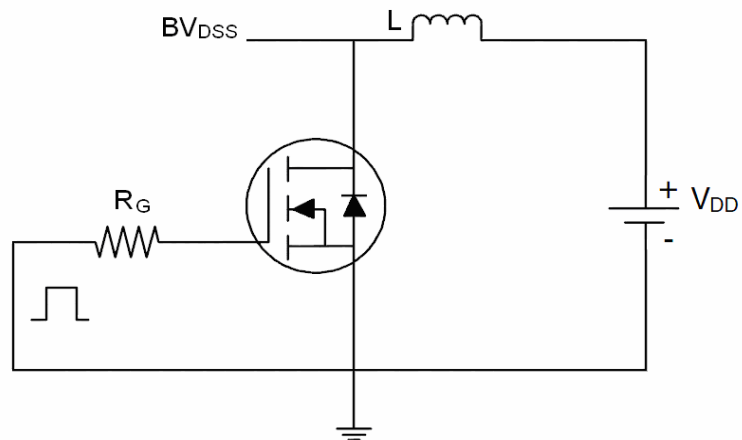
Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V$ $I_D=250\mu A$	100	108	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=100V, V_{GS}=0V$	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 100	nA
On Characteristics ^(Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	3		5	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=150A$	-	1.8	2.1	m Ω
Forward Transconductance	g_{FS}	$V_{DS}=10V, I_D=150A$	-	150	-	S
Dynamic Characteristics ^(Note4)						
Input Capacitance	C_{iss}	$V_{DS}=50V, V_{GS}=0V,$ $F=1.0MHz$	-	18950	-	PF
Output Capacitance	C_{oss}		-	2090	-	PF
Reverse Transfer Capacitance	C_{rss}		-	146	-	PF
Switching Characteristics ^(Note 4)						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=50V, I_D=100A$ $V_{GS}=10V, R_G=1.8\Omega$	-	-	-	nS
Turn-on Rise Time	t_r		-	-	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	-	-	nS
Turn-Off Fall Time	t_f		-	-	-	nS
Total Gate Charge	Q_g	$V_{DS}=50V, I_D=100A,$ $V_{GS}=10V$	-	314		nC
Gate-Source Charge	Q_{gs}		-	115		nC
Gate-Drain Charge	Q_{gd}		-	80		nC
Drain-Source Diode Characteristics						
Diode Forward Voltage ^(Note 3)	V_{SD}	$V_{GS}=0V, I_F=150A$	-		1.2	V
Diode Forward Current ^(Note 2)	I_S		-	-	300	A
Reverse Recovery Time	t_{rr}	$T_J=25^{\circ}C, I_F=I_S$	-	155		nS
Reverse Recovery Charge	Q_{rr}	$di/dt=100A/\mu s$ ^(Note3)	-	436		nC

Notes:

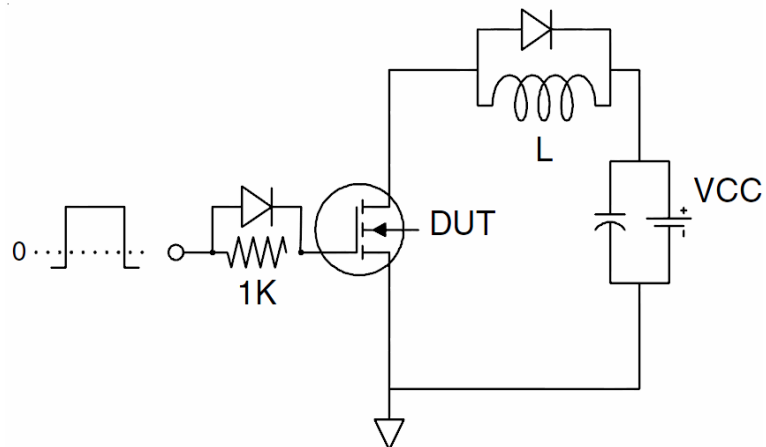
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production
5. EAS condition : $T_J=25^{\circ}\text{C}, V_{DD}=50V, V_G=10V, L=1\text{mH}, R_G=25\Omega$

Test Circuit

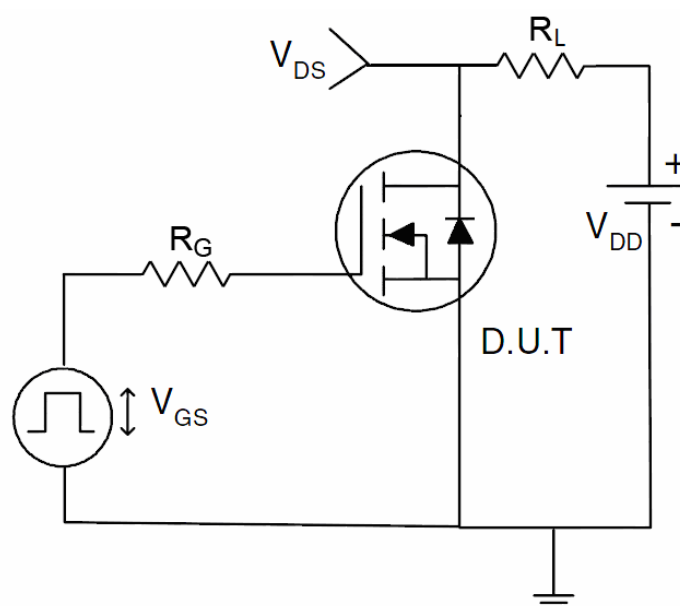
1) E_{AS} test Circuit



2) Gate charge test Circuit



3) Switch Time Test Circuit





Typical Electrical and Thermal Characteristics

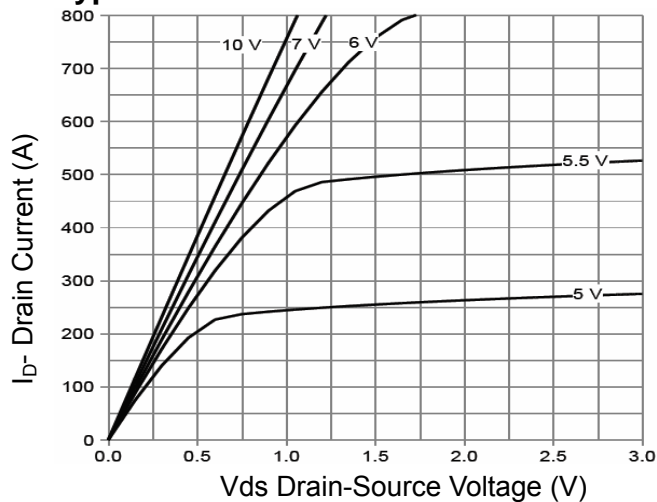


Figure 1 Output Characteristics

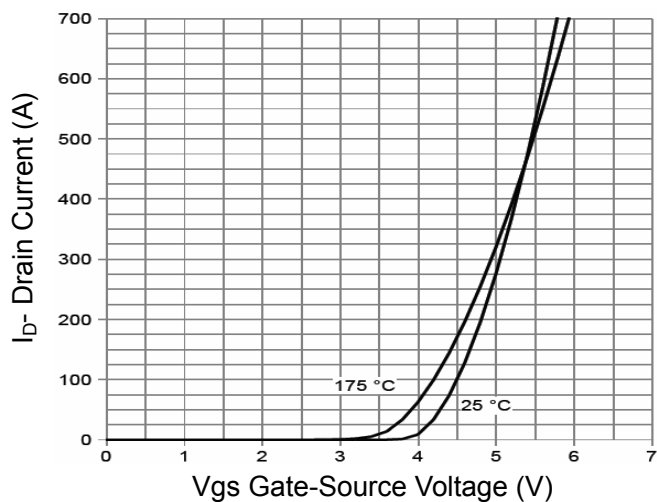


Figure 2 Transfer Characteristics

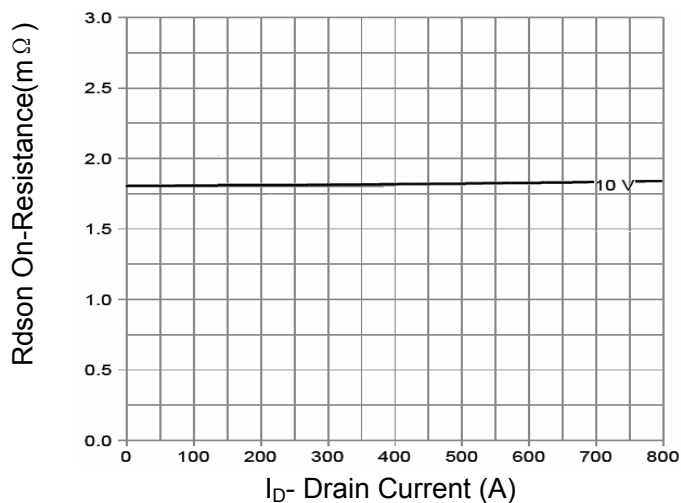


Figure 3 $R_{DS(on)}$ - Drain Current

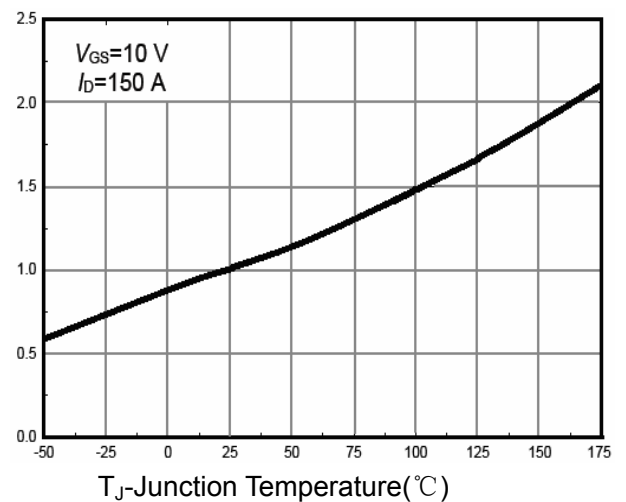


Figure 4 $R_{DS(on)}$ -Junction Temperature

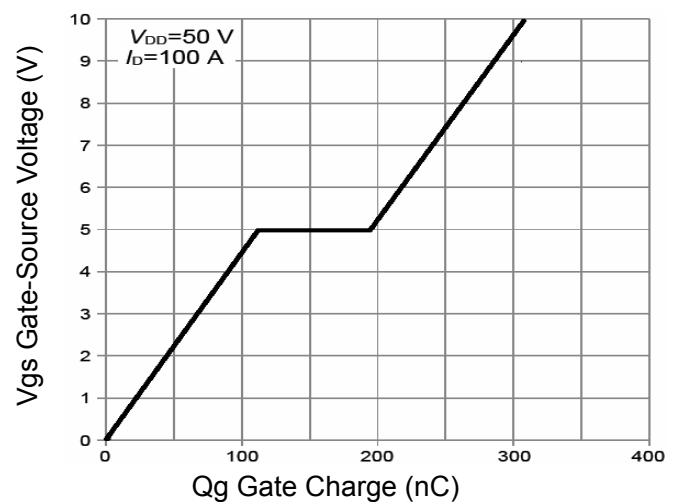


Figure 5 Gate Charge

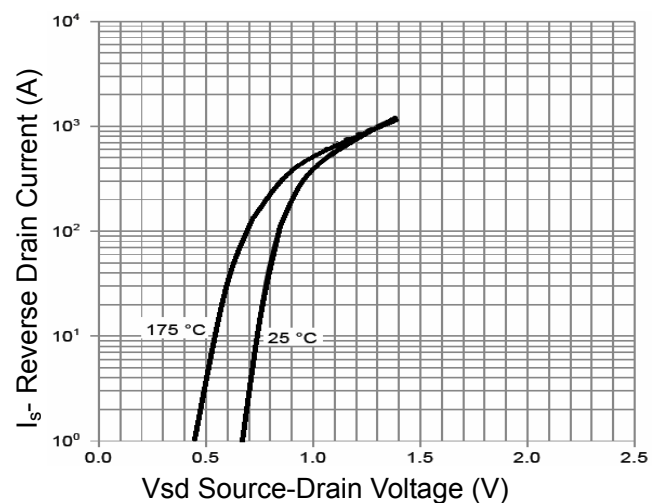


Figure 6 Source- Drain Diode Forward

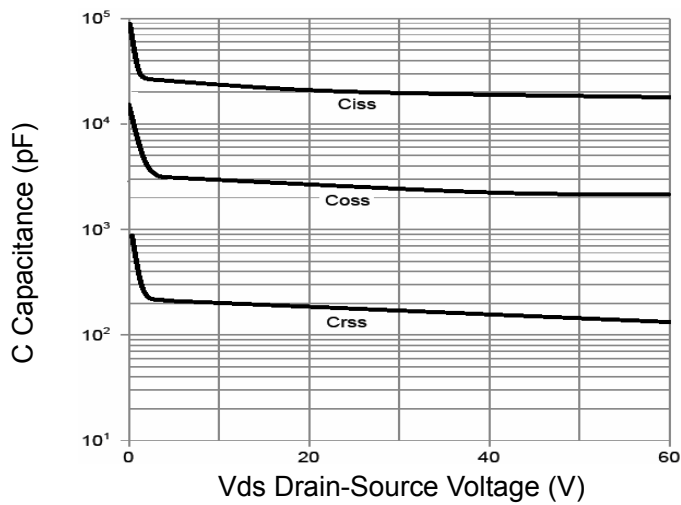


Figure 7 Capacitance vs Vds

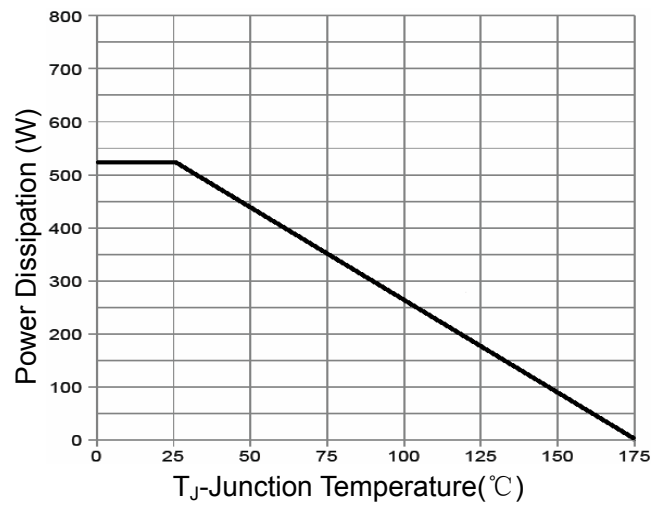


Figure 9 Power De-rating

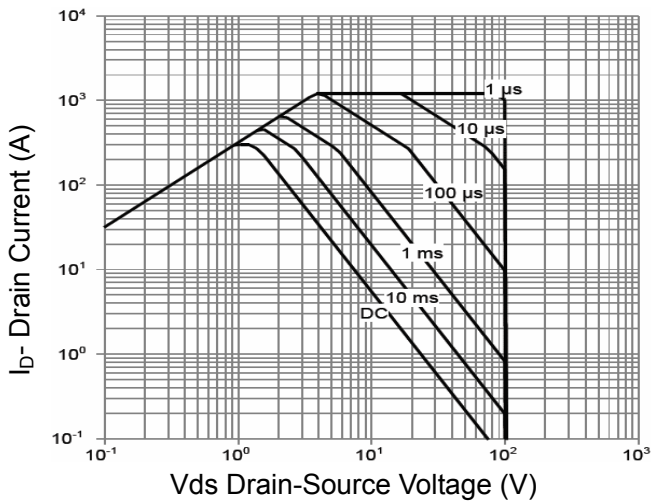


Figure 8 Safe Operation Area

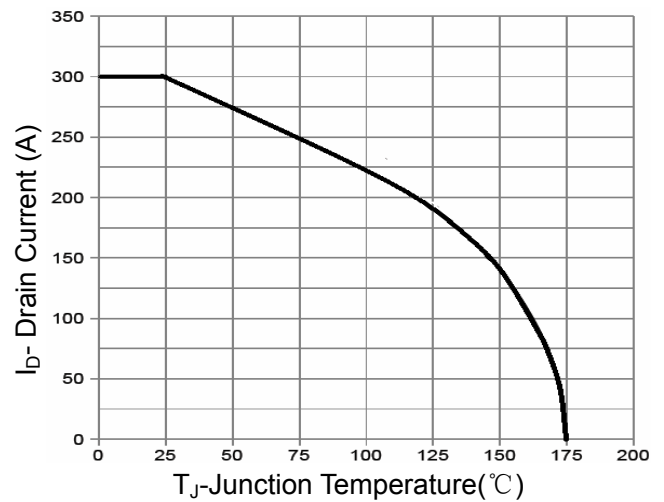


Figure 10 Current De-rating

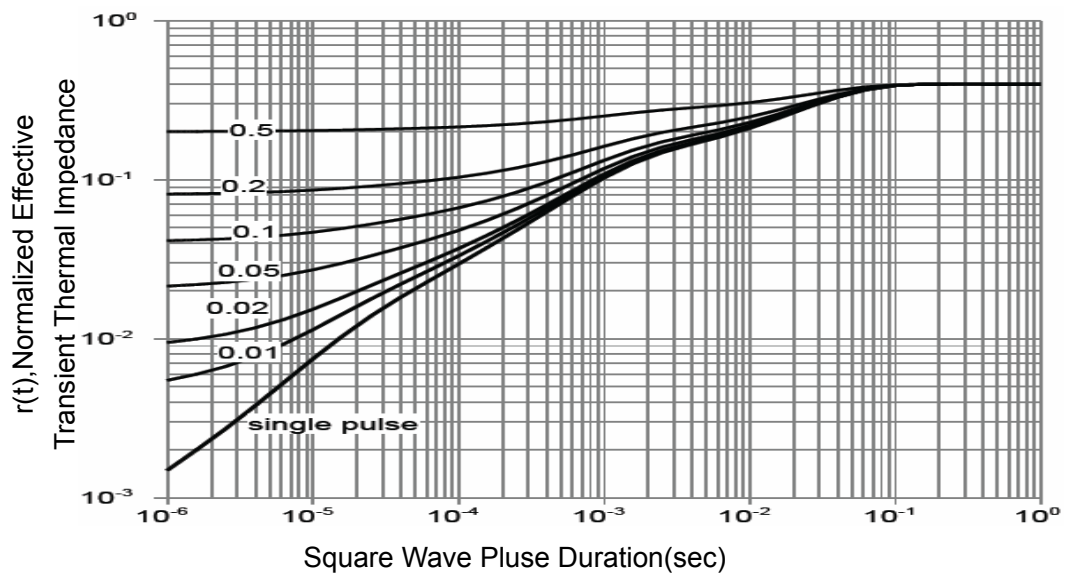
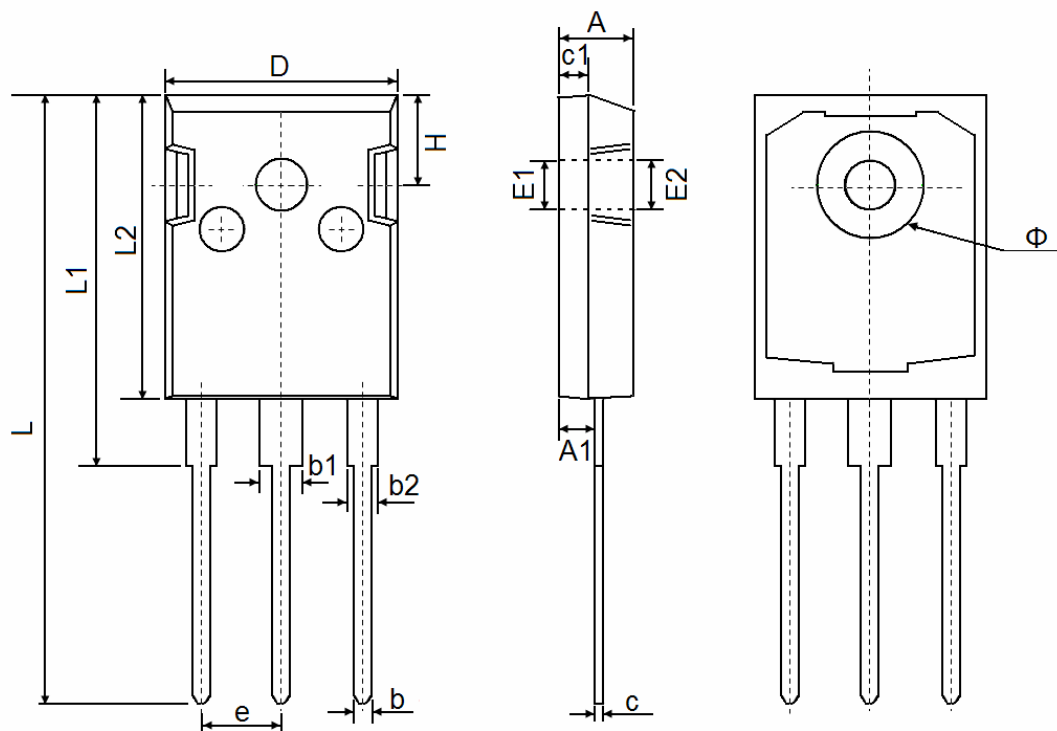


Figure 11 Normalized Maximum Transient Thermal Impedance



TO-247 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.850	5.150	0.191	0.200
A1	2.200	2.600	0.087	0.102
b	1.000	1.400	0.039	0.055
b1	2.800	3.200	0.110	0.126
b2	1.800	2.200	0.071	0.087
c	0.500	0.700	0.020	0.028
c1	1.900	2.100	0.075	0.083
D	15.450	15.750	0.608	0.620
E1	3.500 REF		0.138 REF	
E2	3.600 REF		0.142 REF	
L	40.900	41.300	1.610	1.626
L1	24.800	25.100	0.976	0.988
L2	20.300	20.600	0.799	0.811
Φ	7.100	7.300	0.280	0.287
e	5.450 TYP		0.215 TYP	
H	5.980 REF		0.235 REF	